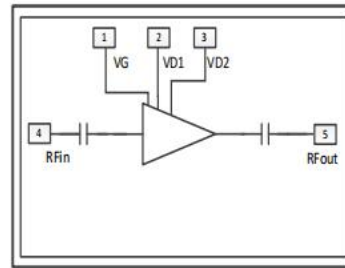


Performance

- Frequency: 8~12GHz
- Typical Signal Gain: 28dB
- Typical Pout: 40.8dBm
- PAE: 43%
- Bias: 28V, -2V
- Technology: 0.25um HEMT
- Size: 2.8*1.5mm*0.08mm

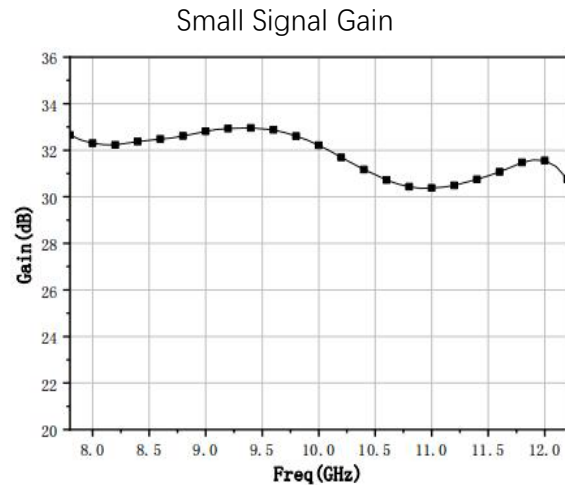
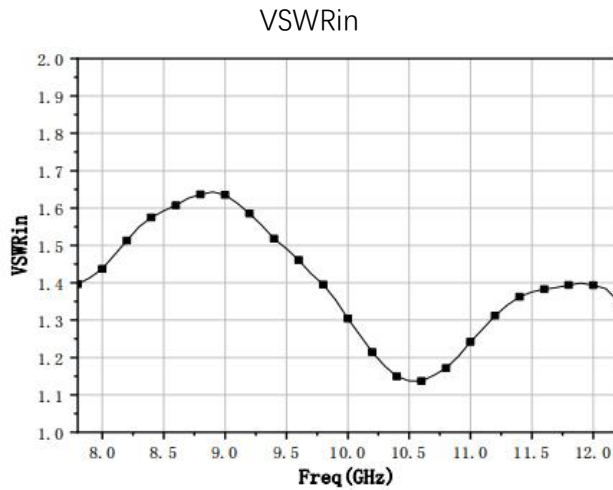
Function Diagram



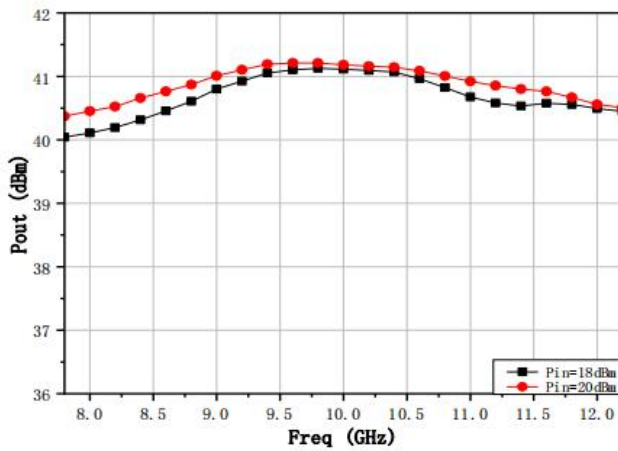
Electrical Specifications (TA=25°C, Vd=28V, Vg=-2.0V, F: 8~12GHz , PL)

Symbol	Parameter	Min	Typical	Max	Unit
G	Small Signal Gain	-	28	-	dB
Gp	Power Gain	-	20	-	dB
Pout	Saturated Power	-	40.8	-	dBm
Id	Dynamic Current	-	1.05	-	A
PAE	Dynamic current	-	43	-	%

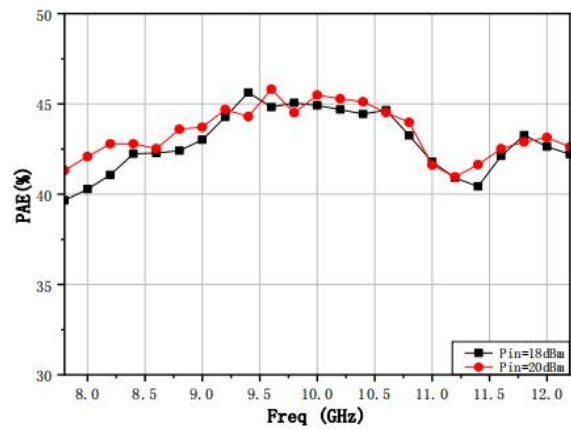
Test Curves



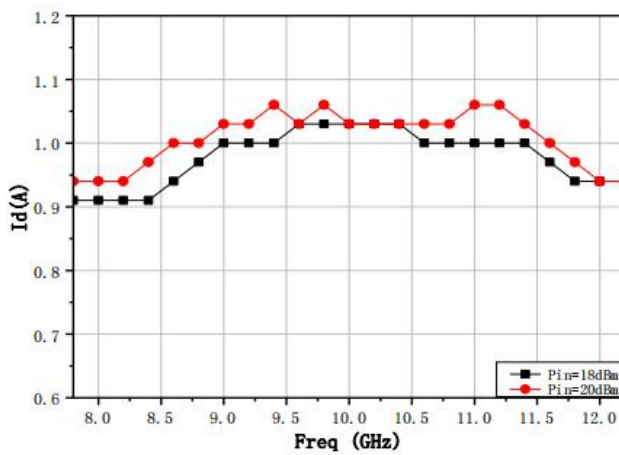
Pout@ Different Pin



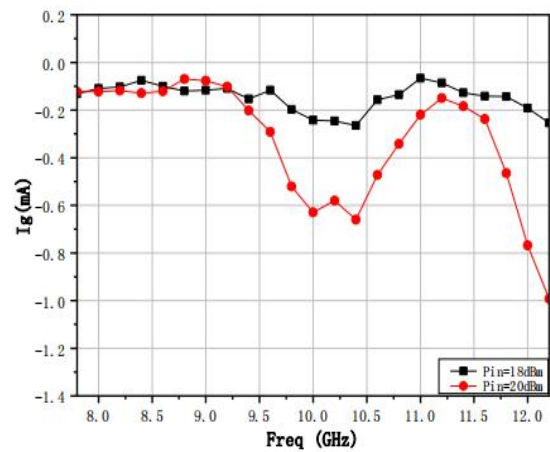
PAE@ Different Pin



Id@ Different Pin



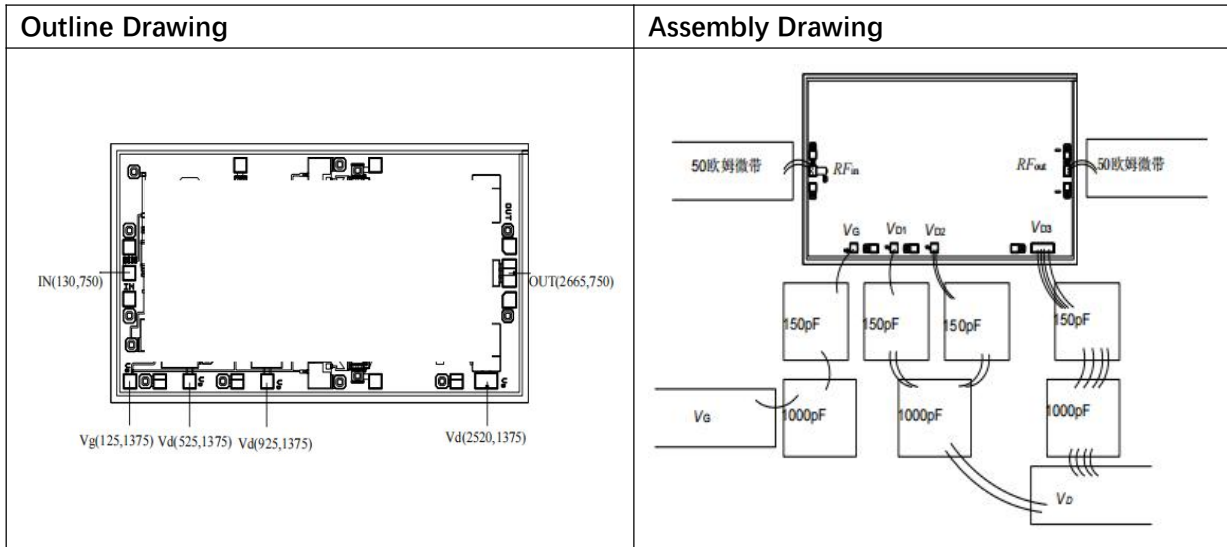
Ig@ Different Pin



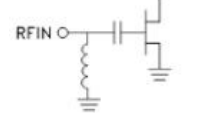
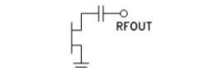
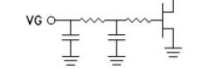

Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	28V	
I _d	Drain Current	1.2A	
P _d	DC Power	20W	
P _{in}	Input Power	25dBm	
T _{ch}	Channel Temperature	225°C	
T _m	Mounting Temperature	310°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

Exceeding any one or combination of these limits may cause permanent damage.



Pads Definition

Pad	Description	Equivalent Circuit
RFin	RF Signal input, connect to 50ohm system, block capacitor is needed if there's external DC applied on this pad.	
RFout	RF Signal output, connect to 50ohm system, no need block capacitor.	
VG	Amp gate bias, external 150pF, 1000pF capacitor is needed	
VD	Amp drain bias, external 150pF, 1000PF capacitor is needed	
GND	Bottom must connect to RF and DC ground	